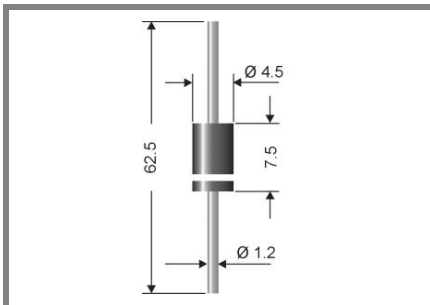


RGP 30K, RGP 30M



Axial lead diode

Fast silicon rectifier diodes

RGP 30K, RGP 30M

Forward Current: 3 A

Reverse Voltage: 800 to 1000 V

Features

- Max. solder temperature: 260°C
- Plastic material has UL classification 94V-0

Mechanical Data

- Plastic case DO-201
- Weight approx.: 1 g
- Terminals: plated terminals solderable per MIL-STD-750
- Mounting position : any
- Standard packaging: 1700 pieces per ammo

1) Valid, if leads are kept at ambient temperature at a distance of 10 mm from case

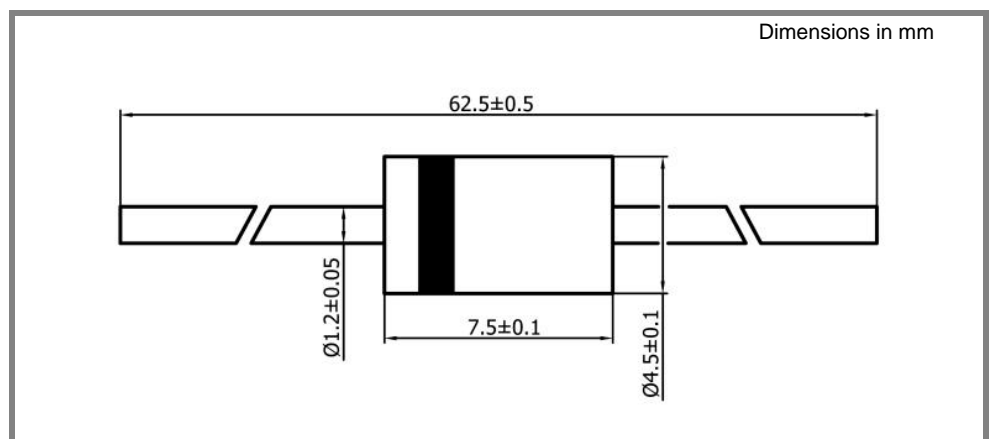
2) $I_F = 3 \text{ A}$, $T_j = 25$

3) $T_A = 25 \text{ °C}$

Type	Repetitive peak reverse voltage	Surge peak reverse voltage	Max. reverse recovery time	Max. forward voltage
	V_{RRM} V	V_{RSM} V	$I_F = 0,5 \text{ A}$ $I_R = 1 \text{ A}$ $I_{RR} = 0,25 \text{ A}$ t_{rr} ns	$V_F^{2)}$
RGP 30K	800	800	500	1,2
RGP 30M	1000	1000	500	1,2

Absolute Maximum Ratings		$T_c = 25^\circ\text{C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
I_{FAV}	Max. averaged fwd. current, R-load, $T_A = 50 \text{ °C}$ ¹⁾	3	A
I_{FRM}	Repetitive peak forward current $f > 15 \text{ Hz}$ ¹⁾	20	A
I_{FSM}	Peak forward surge current 50 Hz half sinus-wave ³⁾	100	A
i^2t	Rating for fusing, $t < 10 \text{ ms}$ ³⁾	50	A ² s
R_{thA}	Max. thermal resistance junction to ambient ¹⁾	25	K/W
R_{thT}	Max. thermal resistance junction to terminals ¹⁾	-	K/W
T_j	Operating junction temperature	-50...+150	°C
T_s	Storage temperature	-50...+175	°C

Characteristics		$T_c = 25^\circ\text{C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
I_R	Maximum leakage current, $T_j = 25 \text{ °C}$; $V_R = V_{RRM}$	<10	μA
	$T_j = \text{°C}$; $V_R = V_{RRM}$		
C_j	Typical junction capacitance (at MHz and applied reverse voltage of V)	-	pF
Q_{rr}	Reverse recovery charge ($U_R = V$; $I_F = A$; $di_F/dt = A/ms$)	-	μC
E_{RSM}	Non repetitive peak reverse avalanche energy ($I_R = \text{mA}$; $T_j = \text{°C}$; inductive load switched off)	-	mJ



case: DO-201

